



6-Pin DIP Optoisolators **Transistor Output**

The MCT and MCT2E devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector.

Applications

- · General Purpose Switching Circuits
- Interfacing and coupling systems of different potentials and impedances
- I/O Interfacing
- Solid State Relays
- Monitor and Detection Circuits
- To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
INPUT LED			
Reverse Voltage	٧R	3	Volts
Forward Current — Continuous	ΙF	60	mA
LED Power Dissipation @ T _A = 25°C with Negligible Power in Output Detector	PD	120	mW
Derate above 25°C		1.41	mW/°C

OUTPUT TRANSISTOR

Collector–Emitter Voltage	VCEO	30	Volts
Emitter–Collector Voltage	VECO	7	Volts
Collector–Base Voltage	VCBO	70	Volts
Collector Current — Continuous	IC	150	mA
Detector Power Dissipation @ T _A = 25°C with Negligible Power in Input LED	PD	150	mW
Derate above 25°C		1.76	mW/°C

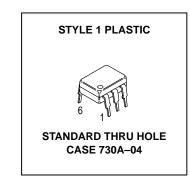
TOTAL DEVICE

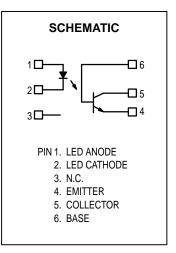
Isolation Surge Voltage(1) (Peak ac Voltage, 60 Hz, 1 sec Duration)	V _{ISO}	7500	Vac(pk)
Total Device Power Dissipation @ T _A = 25°C Derate above 25°C	PD	250 2.94	mW mW/°C
Ambient Operating Temperature Range ⁽²⁾	TA	-55 to +100	°C
Storage Temperature Range(2)	T _{stg}	-55 to +150	°C
Soldering Temperature (10 sec, 1/16" from case)	TL	260	°C

- 1. Isolation surge voltage is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.
- 2. Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.

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MCT2 MCT2E [CTR = 20% Min]







MCT2 MCT2E

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)(1)

Characteristic		Symbol	Min	Typ ⁽¹⁾	Max	Unit
NPUT LED		•		•		•
Forward Voltage (I _F = 20 mA)	T _A = 25°C T _A = -55°C T _A = 100°C	VF	_ _ _	1.23 1.35 1.15	1.5 — —	Volts
Reverse Leakage Current (V _R = 3 V)		I _R		0.01	10	μА
Capacitance (V = 0 V, f = 1 MHz)		СЈ	_	18		pF
OUTPUT TRANSISTOR		•		•		•
Collector–Emitter Dark Current (V _{CE} = 10 V)	T _A = 25°C T _A = 100°C	ICEO	_ _	1	50 —	nA μA
Collector–Base Dark Current (V _{CB} = 10 V)	T _A = 25°C T _A = 100°C	ICBO	_ _	0.2 100	20 —	nA
Collector–Emitter Breakdown Voltage (I _C = 1 mA)		V _(BR) CEO	30	45	_	Volts
Collector–Base Breakdown Voltage (I _C = 10 μA)		V(BR)CBO	70	100	_	Volts
Emitter–Collector Breakdown Voltage (I _E = 100 μA	١)	V(BR)ECO	7	7.8	_	Volts
DC Current Gain (I _C = 5 mA, V _{CE} = 5 V)		hFE	_	500	_	_
Collector–Emitter Capacitance (f = 1 MHz, V _{CE} =	0 V)	C _{CE}	_	7	_	pF
Collector–Base Capacitance (f = 1 MHz, V _{CB} = 0	V)	ССВ	_	19	_	pF
Emitter-Base Capacitance (f = 1 MHz, V _{EB} = 0 V)		C _{EB}	_	9	_	pF
COUPLED		•		•		•
Output Collector Current (I _F = 10 mA, V _{CE} = 10 V)		I _C (CTR) ⁽²⁾	2 (20)	7 (70)	_	mA (%)
Collector–Emitter Saturation Voltage (I _C = 2 mA, I _F = 16 mA)		V _{CE(sat)}	_	0.19	0.4	Volts
Turn–On Time (I _F = 10 mA, V_{CC} = 10 V, R_L = 100 Ω) ⁽³⁾		ton	_	2.8	_	μs
Turn–Off Time (I _F = 10 mA, V_{CC} = 10 V, R_L = 100 Ω ,)(3)		t _{off}	_	4.5	_	μs
Rise Time (I _F = 10 mA, V_{CC} = 10 V, R_L = 100 Ω)(3)		t _r	_	1.2	_	μs
Fall Time (I _F = 10 mA, V_{CC} = 10 V, R_L = 100 Ω)(3)		t _f	_	1.3	_	μs
Isolation Voltage (f = 60 Hz, t = 1 sec)(4)		VISO	7500	_	_	Vac(pk)
Isolation Resistance (V = 500 V)(4)		R _{ISO}	10 ¹¹	_	_	Ω
Isolation Capacitance (V = 0 V, f = 1 MHz)(4)		C _{ISO}		0.2		pF

- 1. Always design to the specified minimum/maximum electrical limits (where applicable).
- 2. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
- 3. For test circuit setup and waveforms, refer to Figure 11.
- 4. For this test, $\,$ Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

TYPICAL CHARACTERISTICS

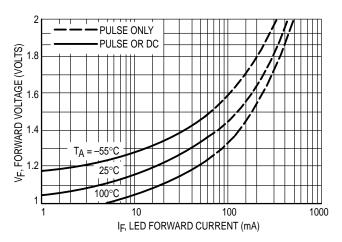


Figure 1. LED Forward Voltage versus Forward Current

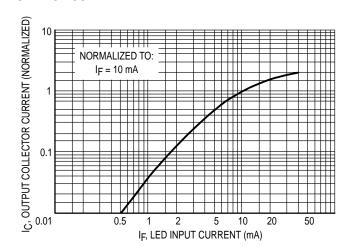


Figure 2. Output Current versus Input Current

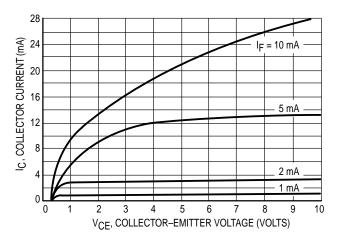


Figure 3. Collector Current versus Collector–Emitter Voltage

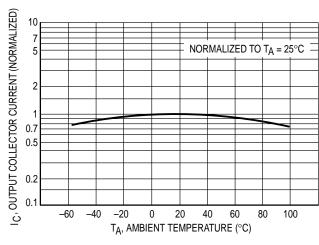


Figure 4. Output Current versus Ambient Temperature

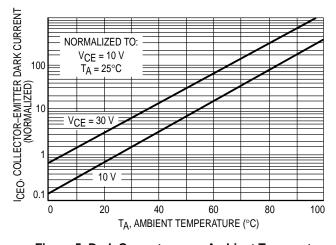


Figure 5. Dark Current versus Ambient Temperature

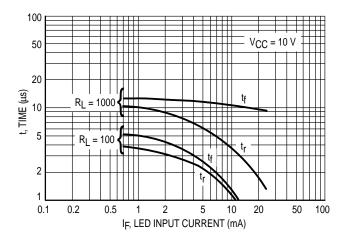


Figure 6. Rise and Fall Times (Typical Values)

MCT2 MCT2E

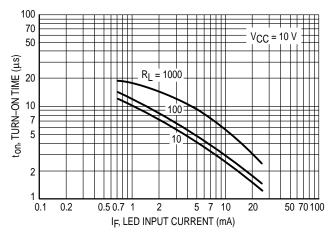


Figure 7. Turn-On Switching Times (Typical Values)

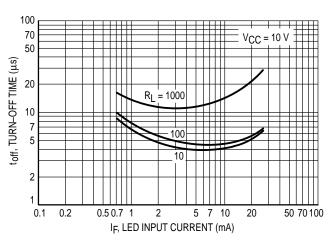


Figure 8. Turn-Off Switching Times (Typical Values)

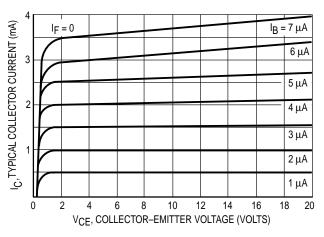


Figure 9. DC Current Gain (Detector Only)

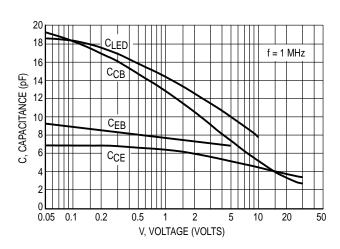


Figure 10. Capacitances versus Voltage

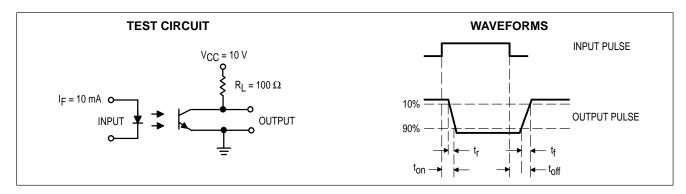
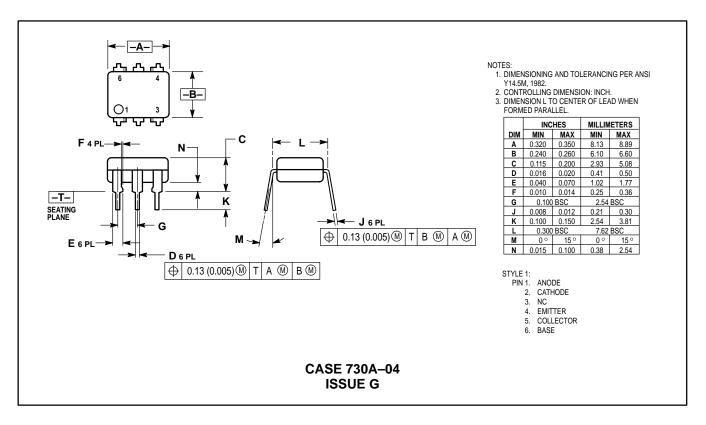
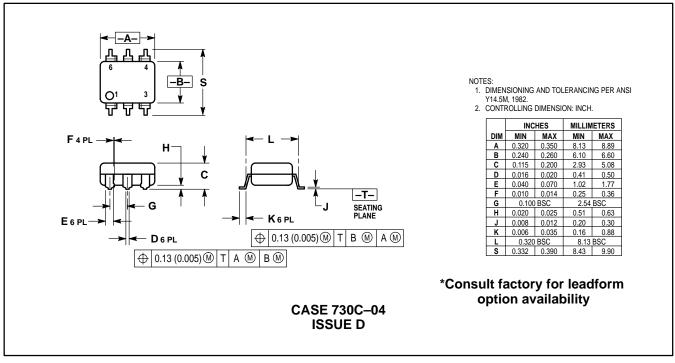


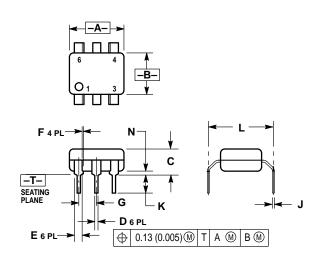
Figure 11. Switching Time Test Circuit and Waveforms

PACKAGE DIMENSIONS





MCT2 MCT2E



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.320	0.350	8.13	8.89	
В	0.240	0.260	6.10	6.60	
С	0.115	0.200	2.93	5.08	
D	0.016	0.020	0.41	0.50	
Е	0.040	0.070	1.02	1.77	
F	0.010	0.014	0.25	0.36	
G	0.100	BSC	2.54	BSC	
J	0.008	0.012	0.21	0.30	
K	0.100	0.150	2.54	3.81	
L	0.400	0.425	10.16	10.80	
N	0.015	0.040	0.38	1.02	

*Consult factory for leadform option availability

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How to reach us:

USA/EUROPE: Motorola Literature Distribution: P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298





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